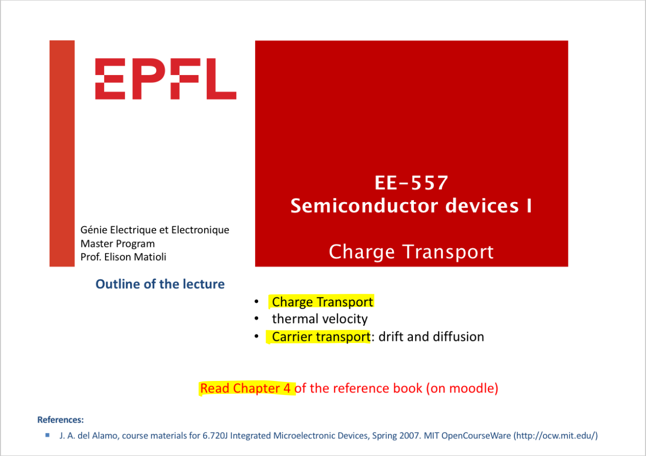
Course 8

Monday, 7 October 2024 14:53

EE557Cours
8 - Charge...



EPFL

EE-557
Semiconductor devices I

Charge Transport

Génie Electrique et Electronique
Master Program
Prof. Elison Matioli

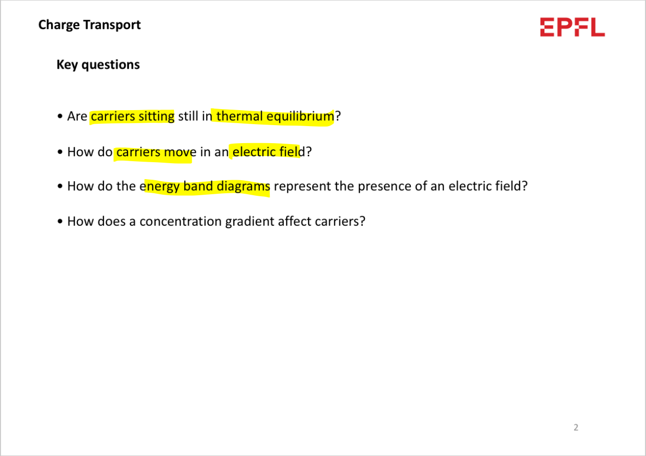
Outline of the lecture

- Charge Transport
- thermal velocity
- Carrier transport: drift and diffusion

Read Chapter 4 of the reference book (on moodle)

References:

- J. A. del Alamo, course materials for 6.720J Integrated Microelectronic Devices, Spring 2007. MIT OpenCourseWare (http://ocw.mit.edu/)



Charge Transport

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Key questions

- Are carriers sitting still in thermal equilibrium?
- How do carriers move in an electric field?
- How do the energy band diagrams represent the presence of an electric field?
- How does a concentration gradient affect carriers?

Carrier flow in semiconductors

Any **motion of free carriers** in a semiconductor leads to a **current**.

Drift:

This motion can be caused by an **electric field** due to an externally applied voltage (electric field), since the carriers are charged particles. We will refer to this transport mechanism as **carrier drift**.

Ex: n-channel MOSFET

Diffusion:

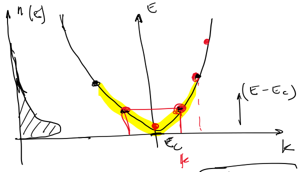
In addition, carriers also move from regions where the **carrier density is high to regions where the carrier density is low**. This carrier transport mechanism is due to the thermal energy and the associated random motion of the carriers. We will refer to this transport mechanism as **carrier diffusion**.

Ex: npn bipolar transistors

The **total current** in a semiconductor equals the **sum** of the **drift and the diffusion** currents.

What happens with electrons at a given temperature without electric field?

thermal velocity



$$v_e(E) = \sqrt{\frac{2(E-E_c)}{m^*_{ce}}}$$

electron conductivity effective mass

Electron velocity

$$v_n(k) = \frac{1}{\hbar} \cdot \nabla_n E(k)$$

at the bottom of Ec

$$E = \frac{\hbar^2 k^2}{2m^*} = \frac{p^2}{2m^*} \Big\}$$

$$v(k) = \frac{\hbar k}{m^*} = \frac{p}{m^*}$$

$p = \hbar k$

classically $p = m \cdot v$

Average thermal velocity,

$$\langle v_{th} \rangle = \frac{\int_{E_c}^{\infty} v_e(E) \cdot n(E)\, dE}{\int_{E_c}^{\infty} n(E)\, dE}$$

on moodle

$$= \sqrt{\frac{8kT}{\pi m^*_{ce}}}$$

For example:

Si at RT, $m^*_{ce} = 0.28\, m_0$ $\Rightarrow$ $\langle v_{th} \rangle = 2 \times 10^7$ cm/s

Thermal motion and scattering

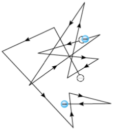
We can think of carriers as particles in **an ideal gas**.

At finite T, carriers have **finite thermal energy**. All this energy resides in the **kinetic energy** of the particles.

Carriers move in **random directions**: no net velocity, but average carrier velocity is thermal velocity:

$$v_{th} = \sqrt{\frac{8kT}{\pi m_c^*}}$$

Zero electric field



$m^*_{ce} \equiv$ **conductivity effective mass** $[eV \cdot s^2/cm^2]$

- This is the effective mass that connects the kinetic energy of an electrons with its velocity
- It accounts for all interactions between the carriers and the perfect periodic potential of the lattice.
- m^*_{ce} and m^*_{ch} are different from the effective mass from the density of states (you can find the values in appendix B on moodle)

For electrons in Si at 300 K (m_{ce}=0.28m_o) and v_{the}=2 × 10^7 cm/s

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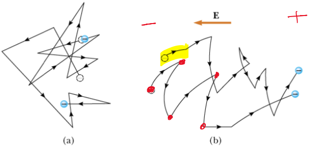
Thermal motion and scattering

But… **semiconductor crystal is not perfect**:

- Atoms themselves are vibrating around their equilibrium position in the lattice
- There are impurities and crystal imperfections.

  As carriers move around, they suffer frequent collisions: **scattering**

Zero electric field **Under electric field E**



- **Mean free path, l_{ce}**: average distance travelled between collisions [cm].
- **Scattering time, τ_{ce}**: average time between collisions [s].

$$\boxed{l_{CE} = \frac{\pi}{4} v_{th} \tau_{CE}}$$

Under $\underline{\vec{E}}$:

$\vec{F} = -q \cdot \vec{E}$

$\underline{\vec{a}} = -\frac{q \cdot \vec{E}}{m_{ce}}$

$v_{drift} = -\frac{q \cdot E}{m_{ce}} \cdot \tau_{ce}$

electron mobility

$$\begin{cases} v_e^{drift} = -\mu_e \cdot E \\ v_h^{drift} = +\mu_h \cdot E \end{cases}$$

μ : $[cm^2/Vs]$

Thermal motion and scattering

↑ scattering ↓ μ

↑ Doping ↓ μ

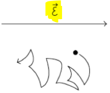
↑ T ↓ μ

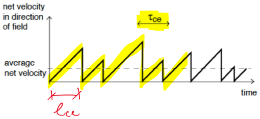
Scattering mechanisms:

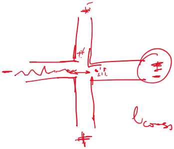
1. Lattice or **phonon scattering**: carriers collide with vibrating lattice atoms
   phonon absorption and emission
   ⇒ some energy exchanged (~ tens of meV)
2. **Ionized impurity scattering**: Coulombic interaction between charged impurities and carriers
   ⇒ no energy exchanged
3. **Neutral impurity scattering** with neutral dopants, interstitials, vacancies, etc
4. **Surface scattering** in inversion layer (surface roughness)
5. **Carrier-carrier scattering (important when carrier concentration is high)**
   Order of magnitude of τ_c < 1 ps
   Then, order of magnitude of l_c < 50 nm

Drift

In the presence of an electric field, electrons drift:







$l_{cross} \ll l_{cc}$

Drift velocity

$$v_e^{drift} = -\frac{q\mathcal{E}\tau_{ce}}{m^*_{ce}}$$

$$v_e^{drift} = -\mu_e\mathcal{E}$$

$$\mu_e \equiv \text{electron mobility } [cm^2/V \cdot s]$$

Electron mobility: Corresponds to the **ease of carrier motion** in response to *E*.
It depends on the **strength of the scattering mechanisms**.

Drift

In the presence of an electric field, electrons drift:

$$\boxed{\begin{array}{c} v_e^{drift} = -\mu_e\mathcal{E} \\ v_h^{drift} = \mu_h\mathcal{E} \end{array}}$$

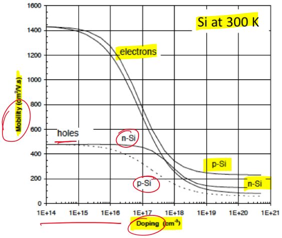
$I = \underline{q} \cdot \underline{n} \cdot v_e$

$v_e = \mu . \vec{E}$

$= q . n . \mu . E$

Mobility depends on:

- **doping level**
- whether carrier is **majority** or **minority-type**.



at low n:

- Mobility is limited by phonon scattering
- thus independent of doping.

at high n:

- Mobility is limited by ionized impurity scattering;
- It is not a strong function of the type of dopant, but only on its concentration.
- Typically, attractive scattering is more pronounced then repulsive: majority carriers have lower mobility

Drift

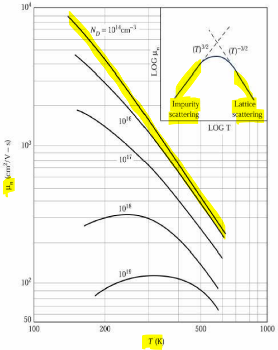
Increasing temperature and increasing doping results in reduction of mobility.

Increasing temperature: increases the number of phonons, which increases the probability that an electron will be scattered by a phonon.

Increasing doping: each dopant atom can scatter electrons.

Thus:

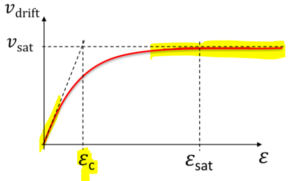
higher doping level -> lower mobility
higher temperature -> lower mobility

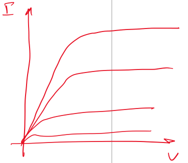


Velocity saturation

The **linear relationship** between drift velocity and electric field **is no longer valid at high fields**

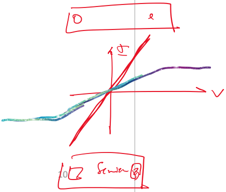
$v \propto E$





Drift velocity vs. electric field fairly well described by: $v^{drift} = \mp \frac{\mu\mathcal{E}}{1+\left|\frac{\mu\mathcal{E}}{v_{sat}}\right|}$

Field required to saturate velocity: $\mathcal{E}_c = \frac{v_{sat}}{\mu}$ $\mathcal{E}_{sat} = 9\mathcal{E}_c$



Velocity saturation crucial in modern devices:

if $\mu = 500\ cm^2/V.s$, $\mathcal{E}_{sat} = 2 \times 10^4\ V/cm$ (2V across 1 μm)

Since μ depends on doping, $\mathcal{E}_{sat}$ depends on doping too.

Velocity saturation

The **linear relationship** between drift velocity and electric field **breaks at high fields**

Implicit assumption:
quasi-equilibrium, that is, scattering rates not much affected from equilibrium.

$$v^{drift} \sim \mathcal{E} \quad \text{only if} \quad v^{drift} \ll v_{th}$$

For **high *E***: carriers acquire substantial energy from *E*
→ optical phonon emission strongly enhanced

scattering time: $\sim 1/\mathcal{E}$

Drift velocity saturates at

$$v_{sat} \simeq \sqrt{\frac{8}{3\pi}\frac{E_{opt}}{m_c^*}}$$

Mobility depends on doping level and whether carrier is majority or minority-type.

For Si at 300 *K*:
- $v_{sat} \sim 10^7\ cm/s$ for electrons
- $v_{sat} \sim 6 \times 10^6\ cm/s$ for holes

Drift current

Particle flux and current density

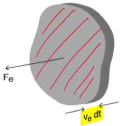
particle flux ≡ # particles crossing unity surface (normal to flow) per unit time [$cm^{-2} \cdot s^{-1}$]

current density ≡ electrical charge crossing unity surface (normal to flow) per unit time [$C \cdot cm^{-2} \cdot s^{-1}$]

$$J_e = -qF_e$$

particle flux: $F_e = \frac{n v_e dt}{dt} = n v_e$ $[cm^{-2}/s]$

$cm^{-3} \cdot cm/s$



Electron and hole current density:

$$J_e = -qn\underbrace{v_e}_{\mu_e|E|}$$

$\frac{C\ cm^{-2}}{s} = [A/cm^2]$

$$J_h = qpv_h$$

Drift current

Drift current (low fields):

$$J_e = q\mu_e n\mathcal{E}$$

$$J_h = q\mu_h p\mathcal{E}$$

Total current:

$$J = q(\mu_e n + \mu_h p)\mathcal{E}$$

Ohm's law for semiconductors

$$\frac{V}{cm} = R\,cm\,\frac{I}{cm^2}$$

$$\rho$$

$$E = (R.cm)\cdot J$$

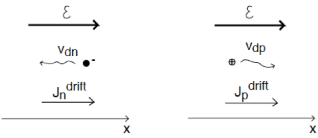
$$J = \frac{E}{\rho} = \sigma\cdot E$$

Electrical conductivity $[(\Omega\cdot cm)^{-1}]$:

$$\sigma = q(\mu_e n + \mu_h p)$$

Electrical resistivity $[\Omega\cdot cm]$:

$$\rho = \frac{1}{q(\mu_e n + \mu_h p)}$$



Drift current

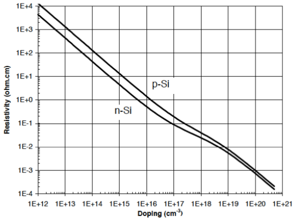
***ρ* strong function of doping** ⇒

frequently used by wafer vendors to specify doping level of substrates

$$\text{-for n-type: } \rho_n \simeq \frac{1}{q\mu_e N_D}$$

$$\text{-for p-type: } \rho_p \simeq \frac{1}{q\mu_h N_A}$$

Si at 300K:

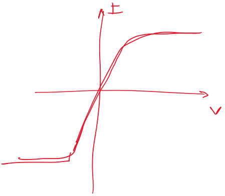


Drift current

Drift current (**high fields**):

$$J_{esat} = qnv_{esat}$$

$$J_{hsat} = qpv_{hsat}$$

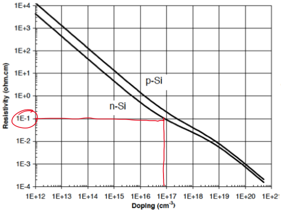


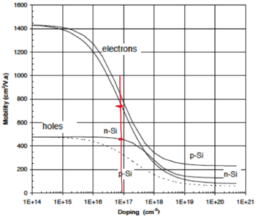
The only way to get **more current at high fields** is to **increase carrier concentration**.

Exercice

Estimate the electrons and holes drift velocity, for a n-type Si with resistivity of 0.1 ohm cm and under an applied field of 1000 V/cm.

Si at 300K:





$N_D = 9\times10^{16}\ cm^{-3} = n_0$

$p_0 = \frac{n_i^2}{n} = \frac{10^{20}}{9\times10^{16}} = 1.1\times10^{3}\ cm^{-3}$

$\mu_e = 750\ cm^2/Vs$

$\mu_h = 460\ cm^2/Vs$

Drift velocity:

$v_e^{drift} = -\mu_e \cdot E = -750\ \frac{cm^{\cancel{2}}}{\cancel{V}s} \times 1000\ \frac{\cancel{V}}{\cancel{cm}} = 750\,000\ cm/s \simeq -7.5\times10^{5}\ cm/s$

$v_h^{drift} = +\mu_h \cdot E = 460\times100 = 4.6\times10^{5}\ cm/s$

vs $v_{th} \sim 2\times10^{7}\ cm/s$

Current densities:

$J_e = -q \cdot n \cdot v_e^{drift} = -1.6\times10^{-19}\ C \times 9\times10^{16}\ cm^{-3} \times (-7.5\times10^{5}\ cm/s) = 1.1\times10^{4}\ A/cm^2$

$[A/cm^2]$

$J_h = +q \cdot p \cdot v_h^{drift} = +1.6\times10^{-19} \times 1.1\times10^{3} \times 4.6\times10^{5} = 9.6\times10^{-11}\ A/cm^2$

$J = J_e = 1.1 \times 10^4 \; A/cm^2$

Drift current

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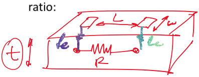
Sheet resistance

The sheet resistance concept is used to characterize both wafers and thin doped layers, since it is typically **easier to measure than the resistivity** of the material.

The sheet resistance of a uniformly doped layer with resistivity, ρ, and thickness, t, is given by their ratio:



$$Rs = \frac{\rho}{t} \qquad \frac{\Omega\,cm}{cm} \qquad \Omega/\square$$

While the unit of the sheet resistance is Ohms, one refers to it as **Ohms per square**.

This nomenclature comes in handy when the resistance of a rectangular piece of material with **length, L**, and **width W** must be obtained. It equals the product of the sheet resistance and the number of squares or:

$$\boxed{R = Rs\frac{L}{W}}$$

Transmission line method (TLM)

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technique to determine the sheet resistance and contact resistance

The sheet resistance of a doped layer with resistivity, ρ, and thickness, t, is:

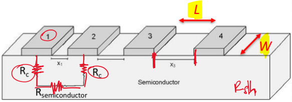
$$Rs = \frac{\rho}{t}$$

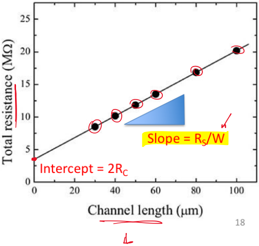
The resistance of a rectangular piece of material with length, L, and width W

$$R = Rs\frac{L}{W}$$

Taking into account the contact resistance (R_c):

$$R = 2R_c + R_S\frac{L}{W}$$





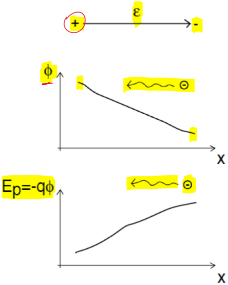
Slope = R_S/W

Intercept = $2R_C$

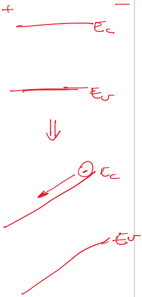
Energy band diagram under electric field

Energy band diagram under electric field:

Energy band diagram needs to account for **potential energy of electric field**



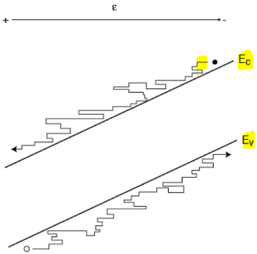
Energy
potential



Electron trades potential energy by kinetic energy as it moves to the left
→ *total electron energy unchanged*

Energy band diagram under electric field

Energy band diagram is **picture of electron energy**
⇒ must add E_p to semiconductor energy band diagram ⇒ bands tilt: **Band bending**



Measuring from an arbitrary energy reference:

$$E_c + E_{ref} = E_p = -q\phi$$

$\frac{eV}{e} = V$

$$\mathcal{E} = -\frac{d\phi}{dx} = \frac{1}{q}\frac{dE_c}{dx} = \frac{1}{q}\frac{dE_v}{dx}$$

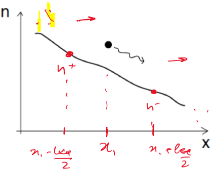
slope of Ec or Ev

Shape of energy bands = shape of *φ* with a minus sign.
Can easily compute *E* from energy band diagram.

Diffusion

Movement of particles from regions of **high concentration to** regions of **low concentration**.

Diffusion produced by collisions with background medium (*i.e.*, vibrating Si lattice).



$$f_e(x) = \frac{n^-}{2} \cdot v_{th} - \frac{n^+}{2} v_{th}$$

$$n^+ - n^- = \frac{dn}{dx}\Big|_{x_1} \cdot l_{ce}$$

$$f_e(x) = \underbrace{-\frac{1}{2} \cdot v_{th} \cdot l_{ce}}_{-D_e} \cdot \frac{dn}{dx}\Big|_{x_1}$$

$$- D_e \cdot \frac{dn}{dx}\Big|_{x_1}$$

Diffusion flux is proportional to the gradient of concentration [Fick's first law]

$$F_e = -D_e \frac{dn}{dx}$$

D_e : $[cm^2/s]$

$$F_h = -D_h \frac{dp}{dx}$$

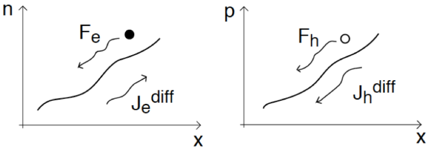
$$D \equiv \text{diffusion coefficient } [cm^2/s]$$

Diffusion

Diffusion current: Electrons and holes are charged particles and their diffusion creates current

$$F_e = -D_e \frac{dn}{dx} \qquad J_e = qD_e \frac{dn}{dx}$$

$$F_h = -D_h \frac{dp}{dx} \qquad J_h = -qD_h \frac{dp}{dx}$$



Non-uniformly doped semiconductor in thermal equilibrium

In summary:

μ relates to "ease" of carrier drift in an electric field.

D relates to "ease" of carrier diffusion as a result of a concentration gradient.

Is there a relationship between μ and D?

- $D_e = \frac{1}{2} v_{th} \cdot l_{ce}$, $l_{ce} = \frac{\pi}{4} \cdot v_{th} \cdot \tau_{ce}$
- $\mu = \frac{q}{m^*_{ce}} \cdot \tau_{ce}$

$$v_{th} = \sqrt{\frac{8}{\pi} \frac{kT}{m^*_{ce}}}$$

$$D_e = \frac{1}{2} \cdot \frac{\pi}{4} \cdot v_{th}^2 \cdot \tau_{ce} = \frac{\cancel{\pi}}{\cancel{8}} \cdot \frac{\cancel{8}}{\cancel{\pi}} \cdot \frac{kT}{m^*_{ce}} \cdot \tau_{ce}$$

$$\frac{D_e}{\mu} = \frac{kT/\cancel{m^*_{ce}} \cdot \cancel{\tau_{ce}}}{q/\cancel{m^*_{ce}} \cdot \cancel{\tau_{ce}}} = \frac{kT}{q}$$

Non-uniformly doped semiconductor in thermal equilibrium

In summary:

μ relates to ”ease” of carrier drift in an electric field.

D relates to ”ease” of carrier diffusion as a result of a concentration gradient.

Is there a relationship between μ and D?

Yes, Einstein relation:

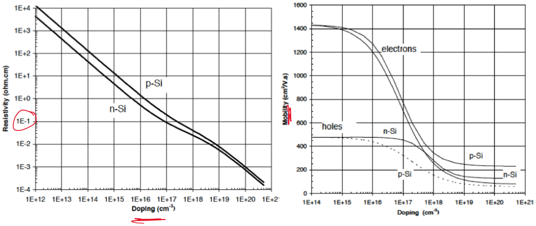
$$\frac{D_e}{\mu_e} = \frac{D_h}{\mu_h} = \frac{kT}{q}$$

Relationship between D and μ only depends on T.

Exercice

Estimate the diffusion coefficients for electrons and holes, for a p-type Si with resistivity of 0.1 ohm cm

Si at 300K:



$\mu \longrightarrow D_e$

Key conclusions

At finite temperatures, carriers move around in a **random way** suffering many collisions: ***thermal motion***.

Dominant scattering mechanisms in bulk Si at 300K: **phonon scattering** and **ionized impurity scattering**.

Two processes for carrier flow in semiconductors: **drift and diffusion**.

General relationship between carrier net velocity (by drift or diffusion) and current density:

$$J_e = -qnv_e \qquad J_h = qpv_h$$

For low fields, $v_{drift} \sim E$
For high fields, $v_{drift} \sim v_{sat}$

Driving force for **diffusion**: **concentration gradient**.

Order of magnitude of key parameters for Si at 300K:

– electron mobility: $\mu_e \sim 100 - 1400\ cm^2/V \cdot s$
– hole mobility: $\mu_h \sim 50 - 500\ cm^2/V \cdot s$
– saturation velocity: $v_{sat} \sim 10^7\ cm/s$

– $v_{th} \sim 2 \times 10^7\ cm/s$
– $\tau_c < 1\ ps$
– $l_c < 50\ nm$